

PNP/PNP high power double bipolar transistor 22 October 2014 P

Product data sheet

1. General description

PNP/PNP high power double bipolar transistor in a SOT1205 (LFPAK56D) Surface-Mounted Device (SMD) power plastic package.

NPN/NPN complement: PHPT610030NK.

NPN/PNP complement: PHPT610030NPK.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Motor control
- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Relay replacement

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	-100	V
I _C	collector current			-	-	-3	А
Per transistor							
R _{CEsat}	collector-emitter saturation resistance	$\begin{split} &I_{C} \texttt{=-2 A; I}_{B}\texttt{=-0.2 A; pulsed;} \\ &t_{p} \texttt{\leq 300 \mu s; } \delta \texttt{\leq 0.02; T}_{amb}\texttt{=25 °C} \end{split}$		-	110	180	mΩ



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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 B2 E2
2	B1	base TR1		
3	E2	emitter TR2		
4	B2	base TR2		
5	C2	collector TR2		E1 B1 C2
6	C2	collector TR2		sym138
7	C1	collector TR1	1 2 3 4 LFPAK56D (SOT1205)	
8	C1	collector TR1		

6. Ordering information

Table 3. Ordering information						
Type number	Package	age				
	Name	Description	Version			
PHPT610030PK	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT610030PK	10030PK

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
Per transistor							
V _{CBO}	collector-base voltage	open emitter		-	-100	V	
V _{CEO}	collector-emitter voltage	open base		-	-100	V	
V _{EBO}	emitter-base voltage	open collector		-	-8	V	
I _C	collector current			-	-3	А	
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-8	А	
IB	base current			-	-0.5	А	
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Symbol	Parameter	Conditions		Min	Мах	Unit
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1	W
			[2]	-	2.4	W
			[3]	-	25	W
Per device		,				,
P _{tot} to	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[4]	-	5	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

- [3] Power dissipation from junction to mounting base.
- [4] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

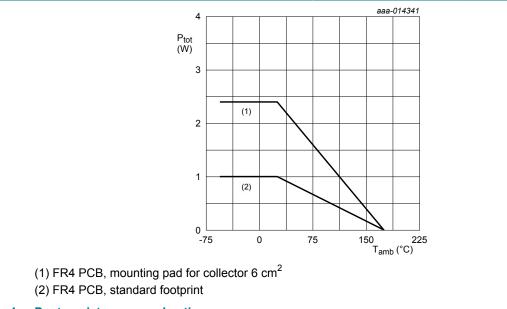


Fig. 1. Per transistor: power derating curves

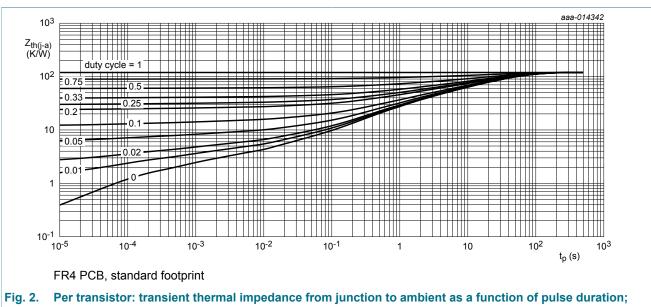
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9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	150	K/W
	from junction to ambient	-	[2]	-	-	62.5	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W
Per device		·					
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	120	K/W
from junction to ambient			[2]	-	-	50	K/W
	ambient		[3]	-	-	30	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

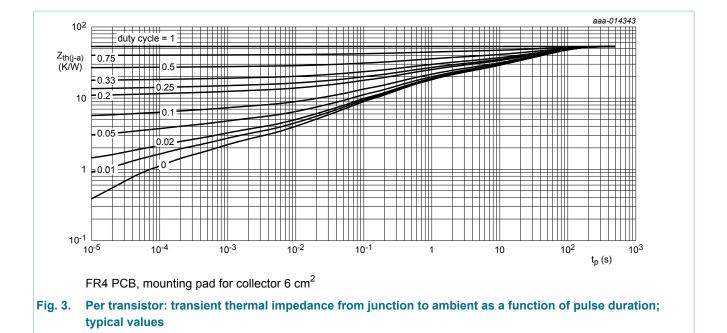


typical values

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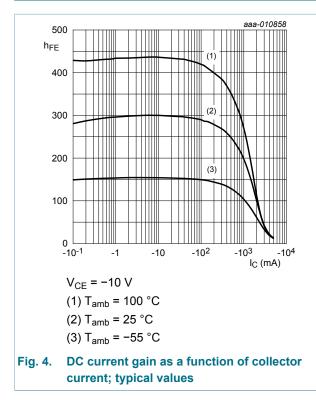
10. Characteristics

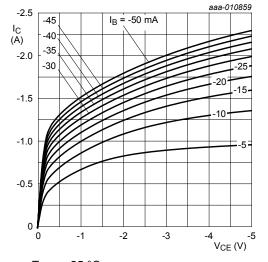
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transist	tor	·				
I _{CBO}	collector-base cut-off	V_{CB} = -80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -80 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -80 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = -7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE} DC current gain	DC current gain	V_{CE} = -10 V; I _C = -500 mA; T _{amb} = 25 °C	150	220	-	
		$\begin{split} V_{CE} &= -10 \text{ V; } I_C = -1 \text{ A; pulsed;} \\ t_p &\leq 300 \mu\text{s; } \delta \leq 0.02\text{; } T_{amb} = 25 ^\circ\text{C} \end{split}$	80	210	-	
		$V_{CE} = -10 \text{ V}; \text{ I}_{C} = -2 \text{ A}; \text{ pulsed};$ $t_{p} \leq 300 \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 ^{\circ}\text{C}$	20	100	-	
		$V_{CE} = -10 \text{ V}; \text{ I}_{C} = -3 \text{ A}; \text{ pulsed};$ $t_{p} \leq 300 \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 ^{\circ}\text{C}$	10	40	-	
OLSAI	collector-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA; T _{amb} = 25 °C	-	-70	-110	mV
		$\begin{split} I_{C} &= -2 \text{ A}; I_{B} = -200 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-220	-360	mV

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{CEsat}	collector-emitter saturation resistance	$\begin{split} I_{C} &= -2 \text{ A}; I_{B} = -0.2 \text{ A}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	110	180	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.91	-1	V
		I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-1.02	-1.2	V
V _{BEon}	base-emitter turn-on voltage	$\label{eq:VcE} \begin{array}{l} V_{CE} = -2 \ V; \ I_{C} = -100 \ mA; \ pulsed; \\ t_{p} \leq 300 \ \mus; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \end{array}$	-	-0.68	-0.9	V
t _d	delay time	V_{CC} = -12.5 V; I _C = -1 A; I _{Bon} = -50 mA;	-	20	-	ns
t _r	rise time	I _{Boff} = 50 mA; T _{amb} = 25 °C	-	180	-	ns
t _{on}	turn-on time		-	200	-	ns
t _s	storage time		-	350	-	ns
t _f	fall time		-	220	-	ns
t _{off}	turn-off time		-	570	-	ns
f _T	transition frequency	V _{CE} = -10 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	-	125	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	30	-	pF





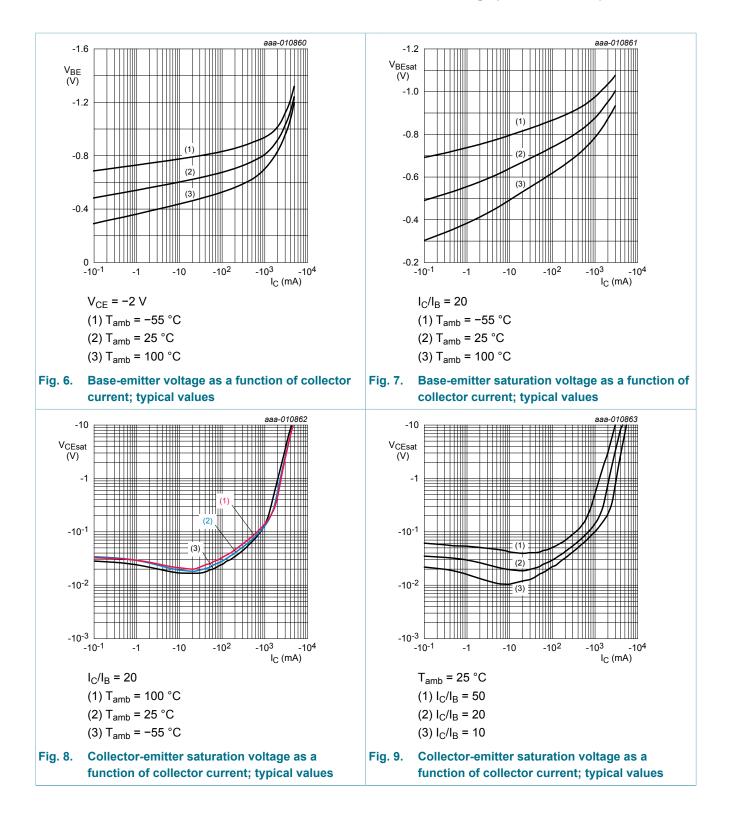
T_{amb} = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values

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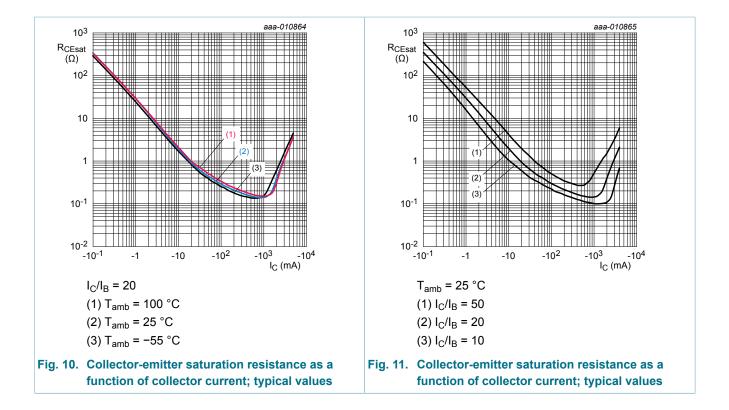
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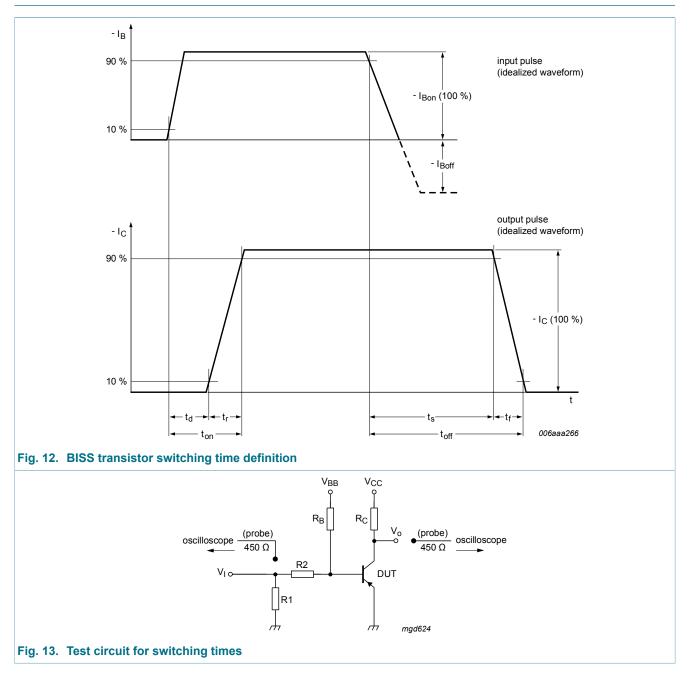
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11. Test information

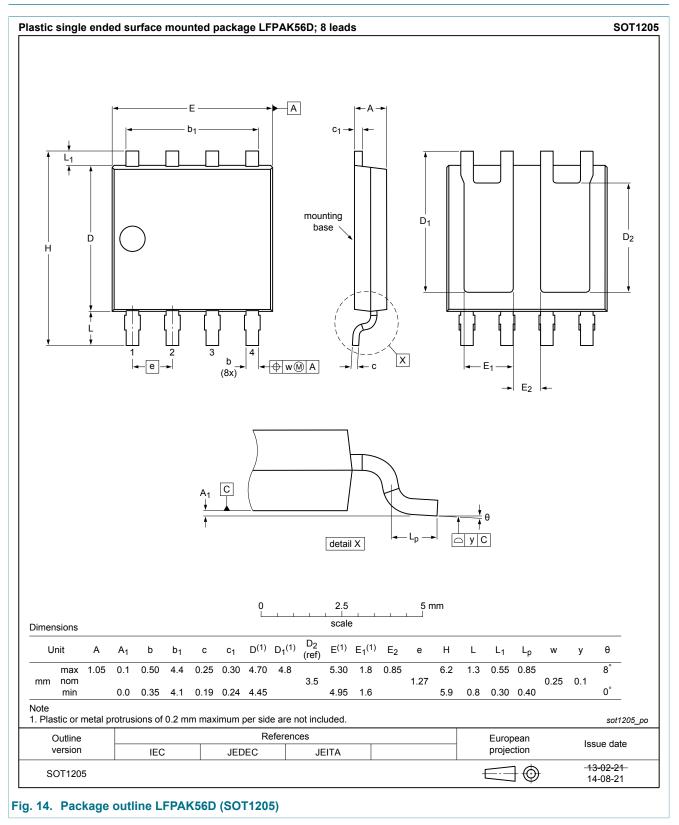
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



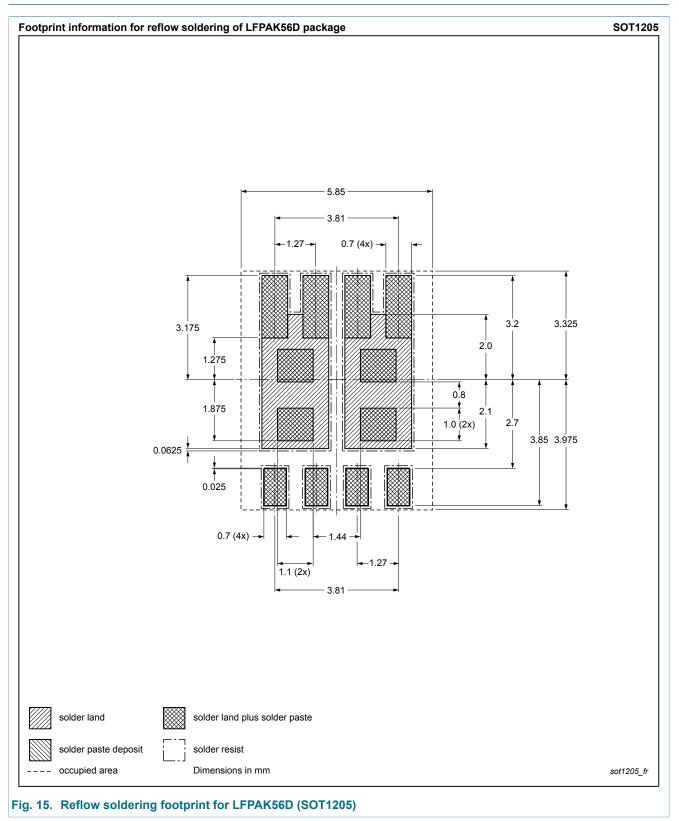
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13. Soldering



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14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PHPT610030PK v.1	20141022	Product data sheet	-	-		

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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